

General Description

The WSR140N08 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

Product Summary

BV_{DSS}	R_{DSON}	I_D
80V	4.8m Ω	140A

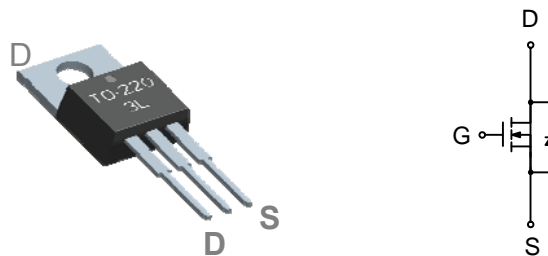
Applications

Power Management for Inverter Systems.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

TO-220FB-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	80	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 140	A
Mounted on Large Heat Sink			
I_{DM}	Pulsed Drain Current *	$T_C=25^\circ\text{C}$ 551**	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 140	A
		$T_C=100^\circ\text{C}$ 91	
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 250	W
		$T_C=100^\circ\text{C}$ 125	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.61	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	
Avalanche Ratings			
E_{AS}	Avalanche Energy, Single Pulsed	$L=0.5\text{mH}$ 762***	mJ

Note : * Repetitive rating ; pulse width limited by junction temperature

** Drain current is limited by junction temperature

*** $V_D=64\text{V}$

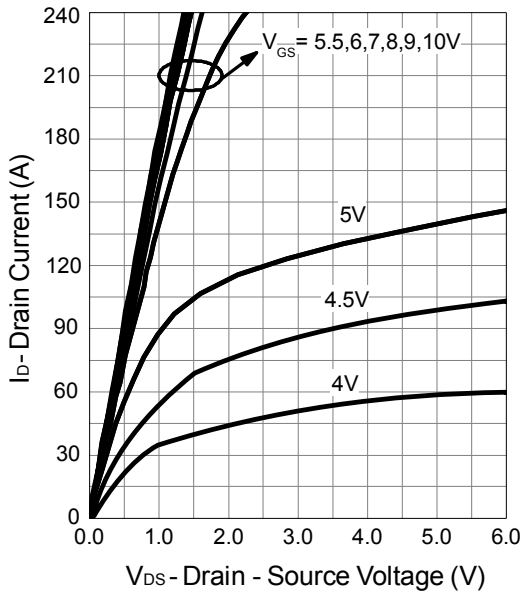
Electrical Characteristics ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	80	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=80V, V_{GS}=0V$ $T_J=85^\circ\text{C}$	-	-	1	μA
			-	-	10	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2.0	3.0	4.0	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$	-	-	± 100	nA
$R_{DS(ON)}^*$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=70A$	-	4.8	6.0	m Ω
Diode Characteristics						
V_{SD}^*	Diode Forward Voltage	$I_{SD}=70A, V_{GS}=0V$	-	0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=70A, di_{SD}/dt=100A/\mu s$	-	30	-	ns
Q_{rr}	Reverse Recovery Charge		-	52	-	nC
Dynamic Characteristics						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	-	1.6	-	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=25V,$ Frequency=1.0MHz	-	4687	-	pF
C_{oss}	Output Capacitance		-	665	-	
C_{rss}	Reverse Transfer Capacitance		-	235	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=40V, R_G=6\Omega,$ $I_{DS}=70A, V_{GS}=10V,$	-	26	-	ns
T_r	Turn-on Rise Time		-	17	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	41	-	
T_f	Turn-off Fall Time		-	53	-	
Gate Charge Characteristics						
Q_g	Total Gate Charge	$V_{DS}=64V, V_{GS}=10V,$ $I_{DS}=70A$	-	115	-	nC
Q_{gs}	Gate-Source Charge		-	15	-	
Q_{gd}	Gate-Drain Charge		-	44	-	

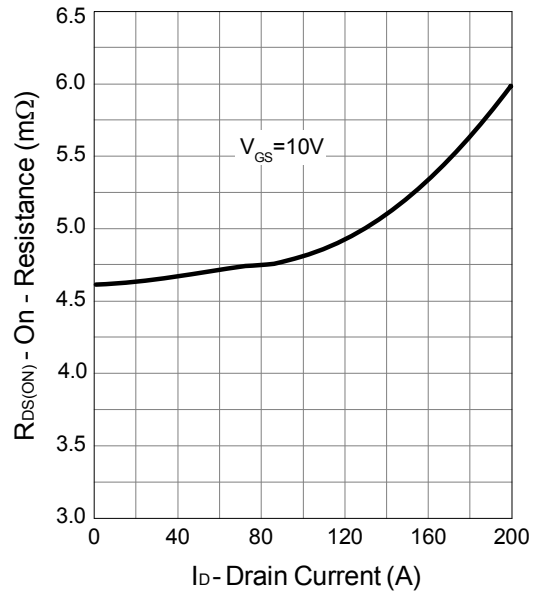
Note * : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Typical Operating Characteristics

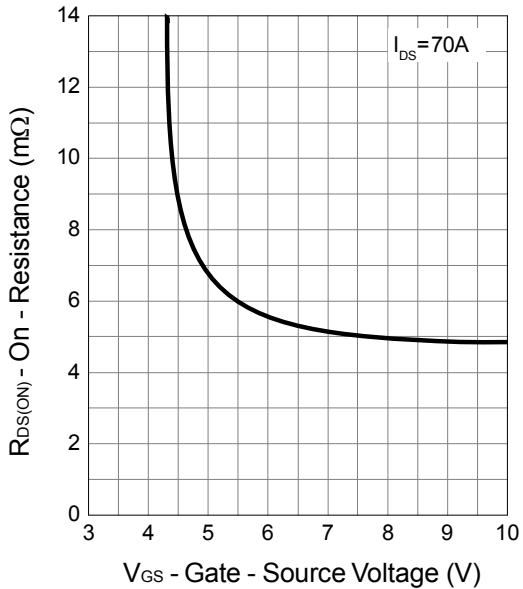
Output Characteristics



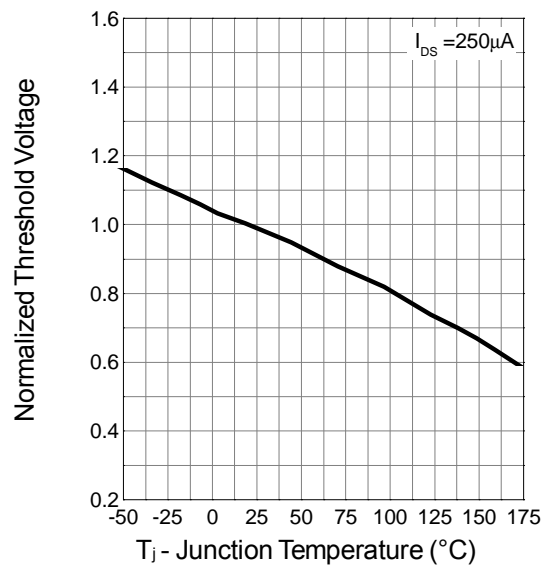
Drain-Source On Resistance



Gate-Source On Resistance

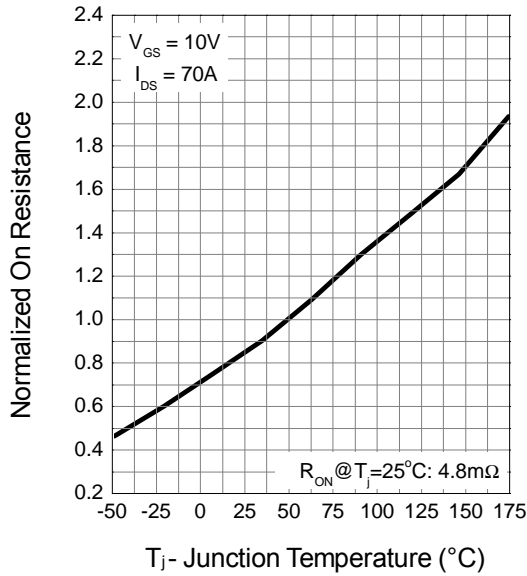


Gate Threshold Voltage

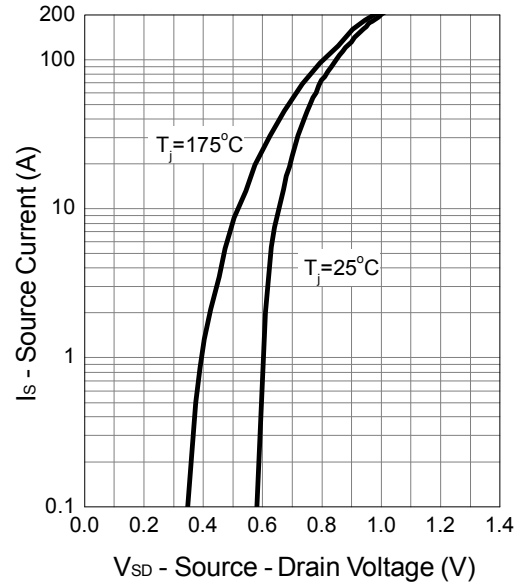


Typical Operating Characteristics (Cont.)

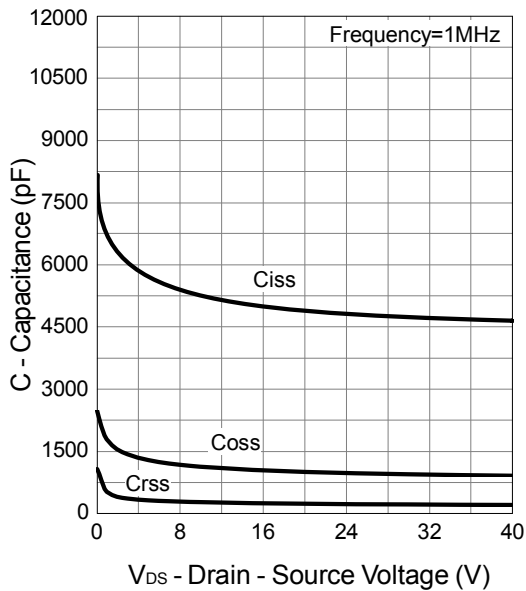
Drain-Source On Resistance



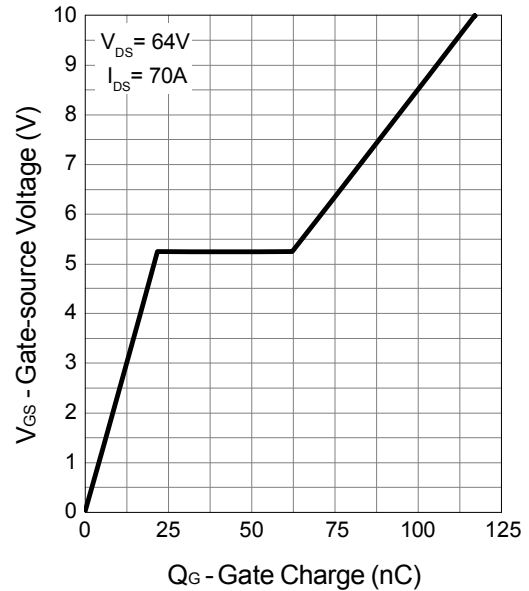
Source-Drain Diode Forward



Capacitance

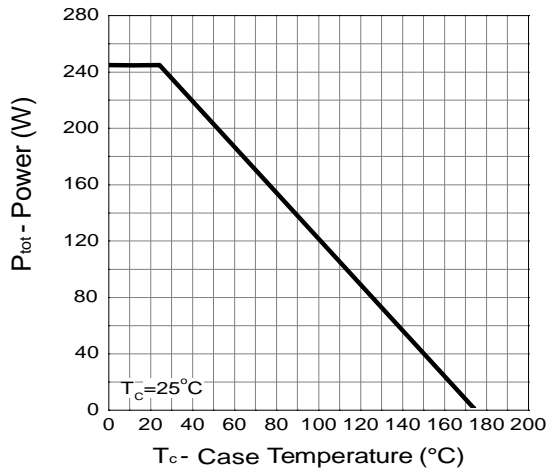


Gate Charge

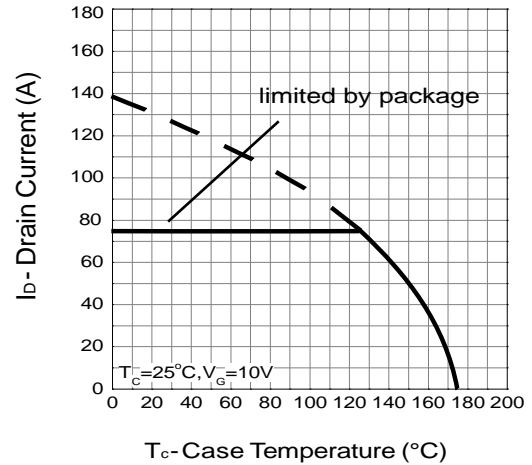


Typical Operating Characteristics (Cont.)

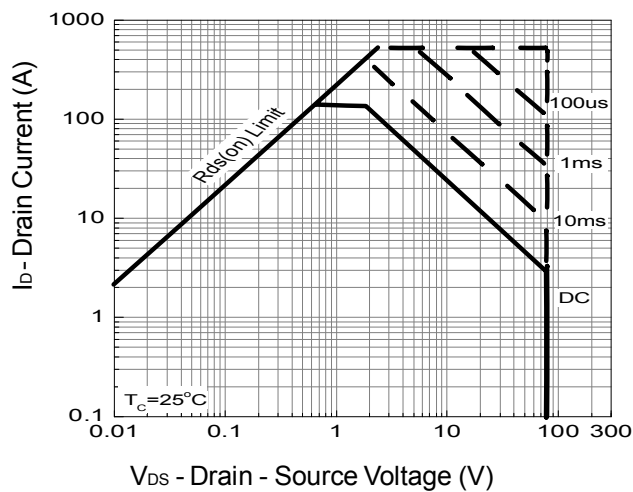
Power Dissipation



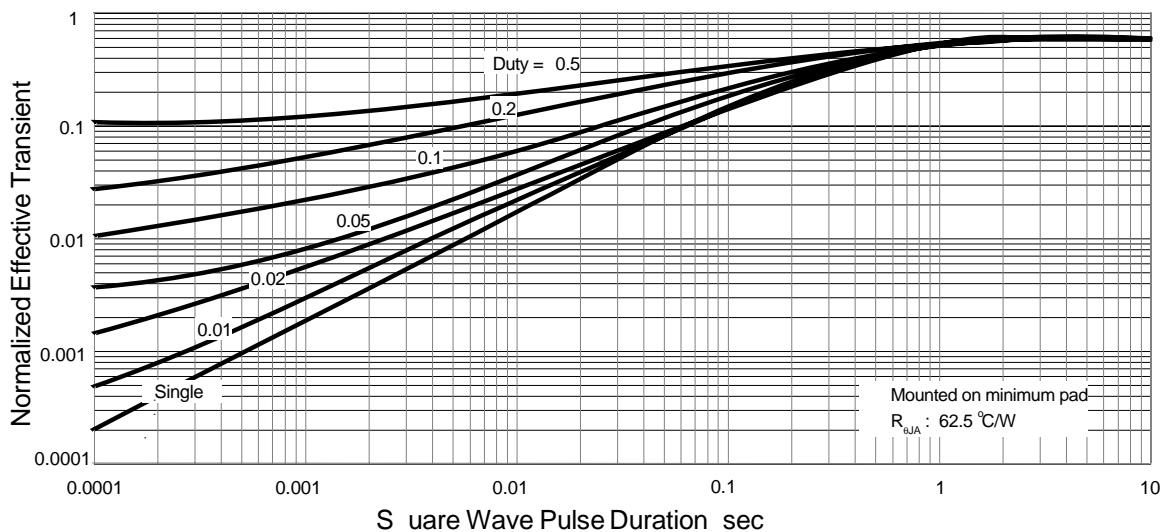
Drain Current

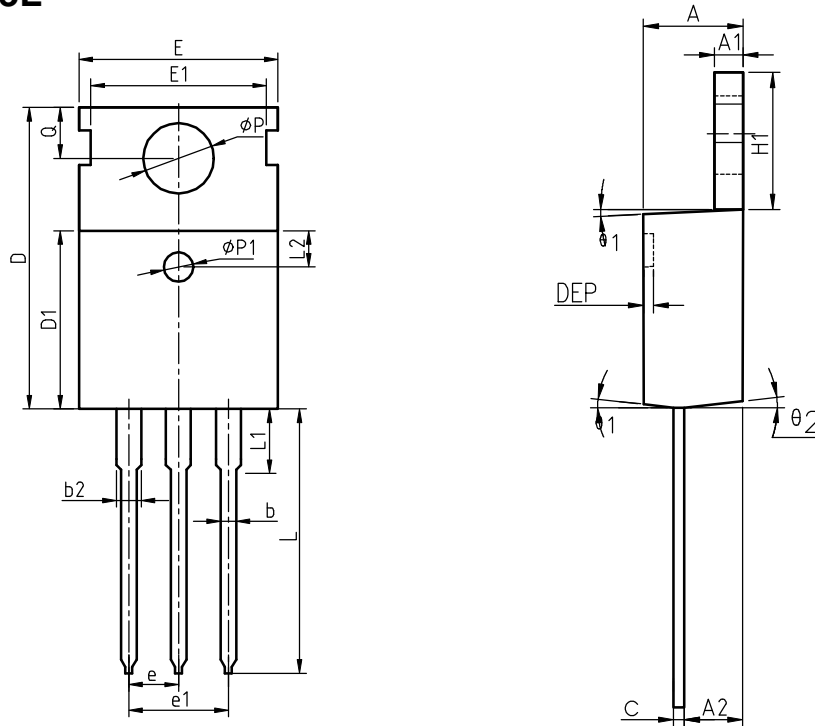


Safe Operation Area



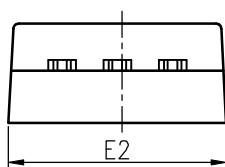
Thermal Transient Impedance



Package Information
TO-220FB-3L


COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1.27	1.36	0.046	0.050	0.054
c	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.80	10.00	10.20	0.386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
e		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
P	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
theta 1	5°	7°	9°	5°	7°	9°
theta 2	1°	3°	5°	1°	3°	5°
theta 3	1°	3°	5°	1°	3°	5°





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